HEMT用GaN on Si基板

GaN Epitaxial Films on Si Substrates for HEMT Devices

次世代パワーデバイスや高周波デバイスの本命
Best Choice for Next Generation Power Devices and RF Devices

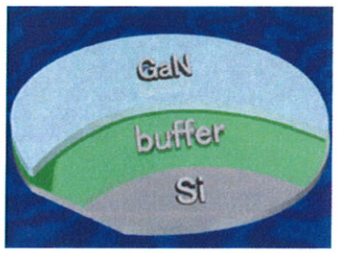
特長　Features

- **高い縦耐圧**
  High Vertical Breakdown Voltage (180V/μm)
- **エピタキシャル総膜厚6μmでも反り制御可能**
  Warpage Control : at 6μm Epitaxial Layers
- **Si基板はCZ法に加え、MCZ法が対応可能**
  Si Substrate Type : CZ and MCZ

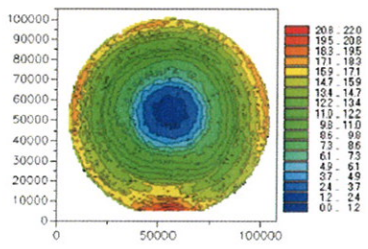
基板仕様　Characteristics

Typical Data	
Heteroepitaxial layer	GaN
Intermediate buffer layer	proprietary
Si Substrate compatibility with	CZ & MCZ~ϕ3,4,(6)inch
Breakdown voltage	>600V(~1kV)
Dislocation density	≦5x10^{9}cm^{-2}
Crystallinity(XRD-FWHM)	≦1000arc secs
AlGaN/GaN-HEMT structure	on demand
-Mobility of 2DEG	>1200cm^{2}/Vs
-Al conc. uniformity(σ/mean)	≦2%
Frontsurface	as grown
Backsurface	Si etched

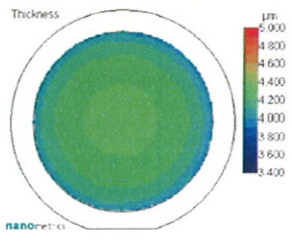
※Edge Exclusion 10mm



Heteroepitaxial growth
using buffer layers



Warpage ≦ 40μm



Thickness Uniformity σ/mean ≦ 3%

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